

# BRMJD45DP

Rev.A Nov.-2023

## 描述 / Descriptions

TO-252 塑封封装 PNP 半导体三极管。

Silicon PNP transistor in a TO-252 Plastic Package.

## 特征 / Features

与 BRMJD44DP 互补，无卤产品。

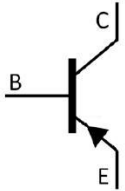
Complement to BRMJD44DP, HF product.

## 用途 / Applications

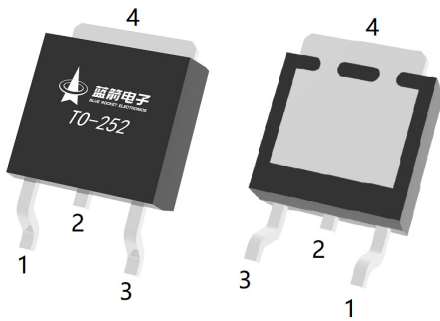
用于中功率线性开关。

Medium power linear switching applications.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : Base

PIN 2,4 : Collector

PIN 3 : Emitter

## 放大及印章代码 / h<sub>FE</sub> Classifications & Marking

见印章说明。

See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V <sub>CBO</sub>	-80	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-80	V
Emitter to Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current - Continuous	I <sub>C</sub>	-8.0	A
Collector Peak Current	I <sub>CM</sub>	-16.0	A
Collector Power Dissipation	P <sub>D</sub> (T <sub>A</sub> =25°C)	1.75	W
Collector Power Dissipation	P <sub>D</sub> (T <sub>C</sub> =25°C)	20	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Emitter Breakdown Voltage	V <sub>CEO</sub>	I <sub>C</sub> = -30mA I <sub>B</sub> = 0	-80			V
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> = -80V V <sub>BE</sub> = 0			-1.0	μA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>BE</sub> = -5.0V I <sub>C</sub> = 0			-1.0	μA
DC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -1.0V I <sub>C</sub> = -2.0A	60		250	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -1.0V I <sub>C</sub> = -4.0A	40			
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -8.0A I <sub>B</sub> = -400mA			-1	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -8.0A I <sub>B</sub> = -800mA			-1.5	V
Current- Gain Bandwidth Product	f <sub>T</sub>	I <sub>C</sub> = -0.5A f = 20MHz V <sub>CE</sub> = -10V		90		MHz

电参数曲线图 / Electrical Characteristic Curve

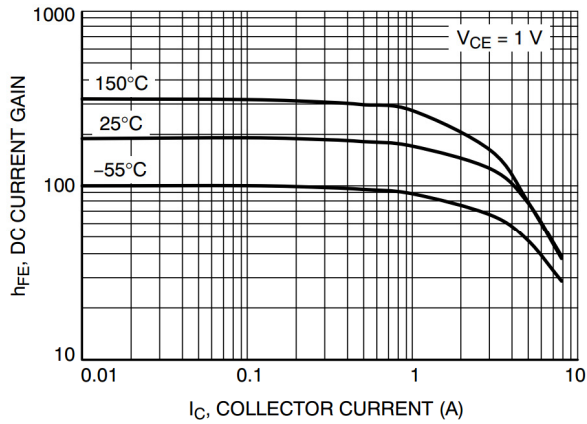


Figure 1. DC Current Gain

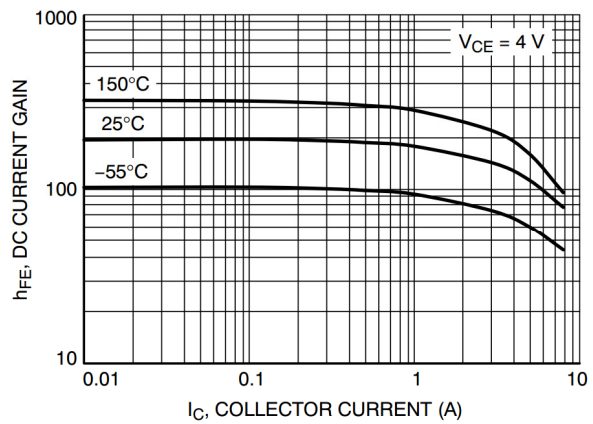


Figure 2. DC Current Gain

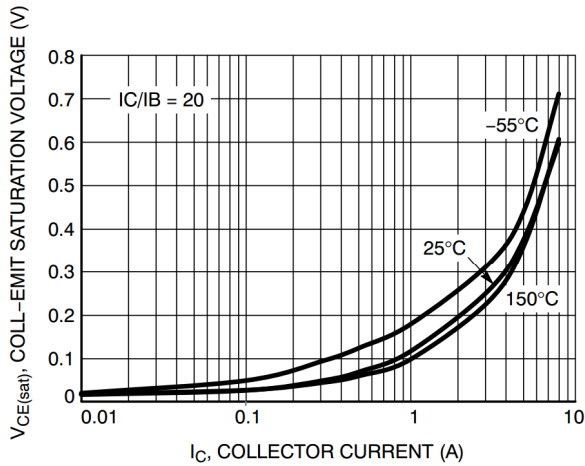


Figure 3. Saturation Voltage

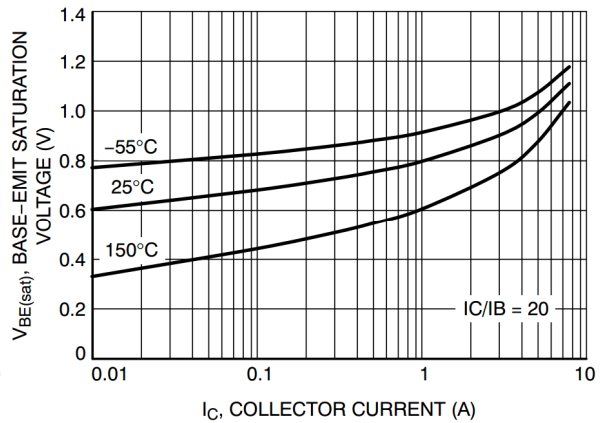


Figure 4. Saturation Voltage

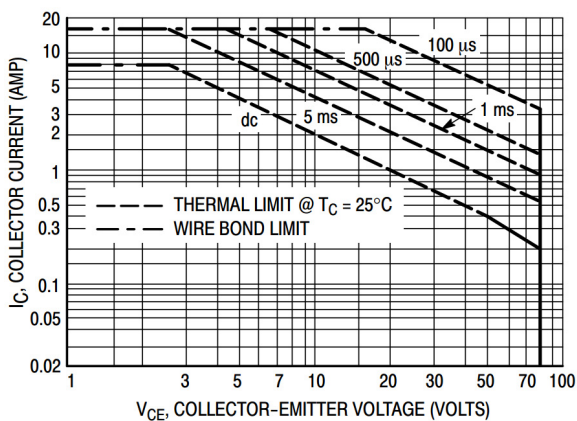
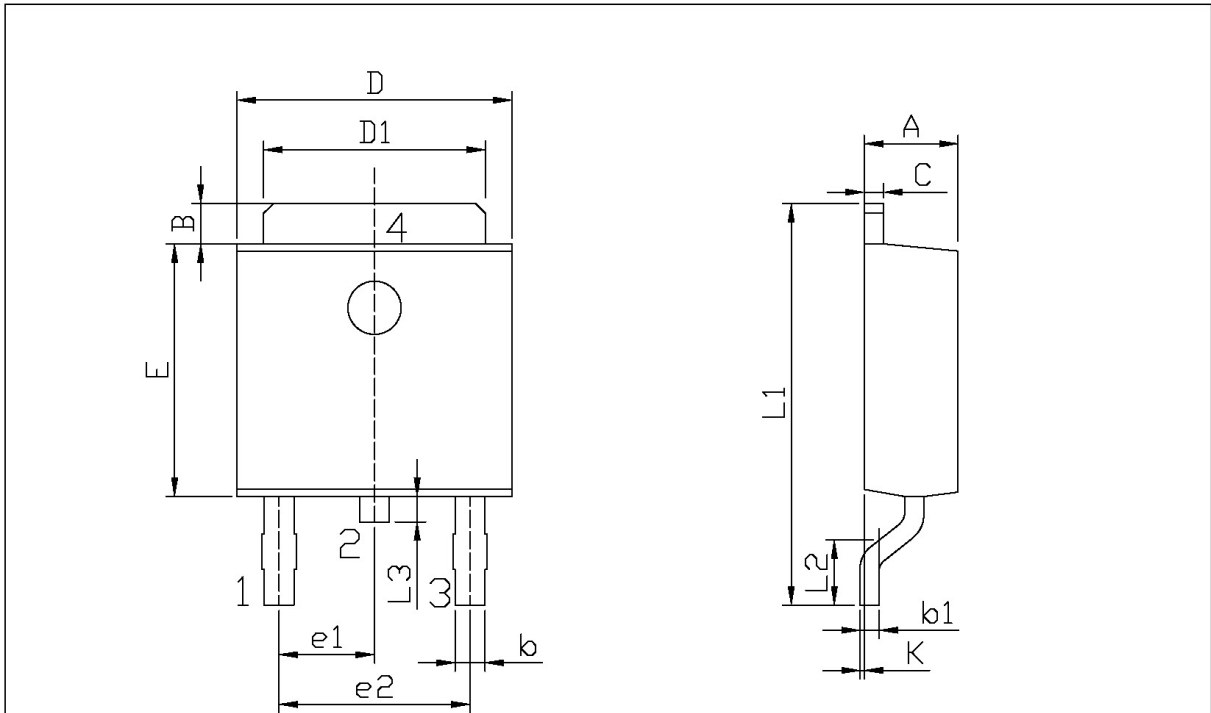


Figure 5. Maximum Forward Bias Safe Operating Area

外形尺寸图 / Package Dimensions

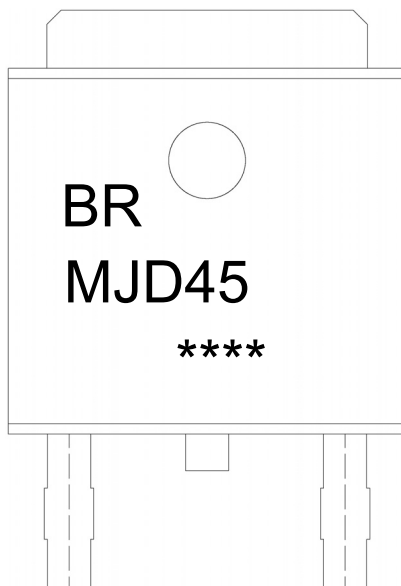


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

## 印章说明 / Marking Instructions



说明：

BR： 为公司代码

MJD45： 为型号代码

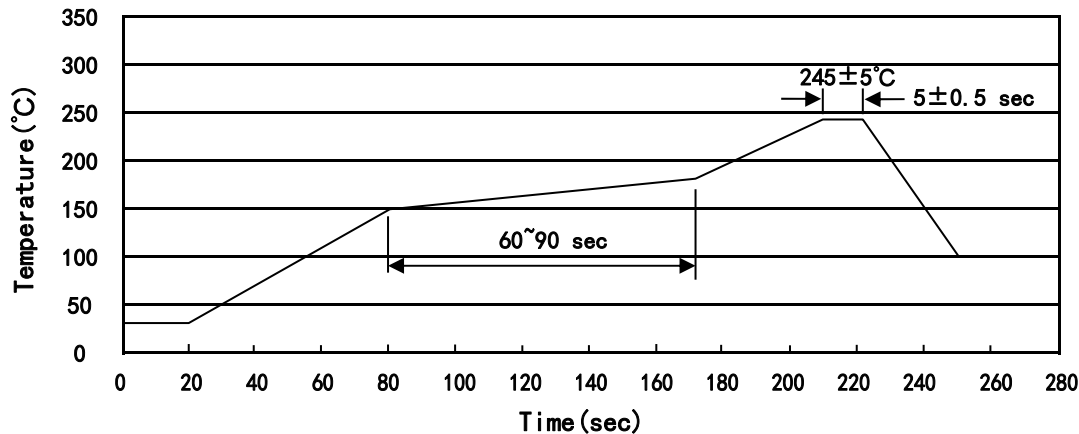
\*\*\*\*： 为生产批号代码，随生产批号变化

Note:

BR: Company Code

MJD45: Product Type Code

\*\*\*\*: Lot No. Code, code change with Lot No

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

**使用说明 / Notices**